Abstracts

Cost-Effective High Performance Monolithic X-Band Low Noise Amplifiers (1986 [MCS])

D.C. Wang, R.G. Pauley, S.K. Wang and L.C.T. Liu. "Cost-Effective High Performance Monolithic X-Band Low Noise Amplifiers (1986 [MCS])." 1986 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 86.1 (1986 [MCS]): 61-63.

A low cost and high performance X-band low-noise amplifier with ion-implanted MESFET technology has been demonstrated. Various design, material, and processing approaches have been evaluated in terms of yield, cost, and device performance. An average noise figure of 2.2 dB and standard deviation of 0.1 dB with an associated gain of 22.5 dB and standard deviation of 0.8 dB at center frequency band of 9.5 GHz has been measured.

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